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Sommario/riassunto

The field of charge conduction in disordered materials is a rapidly evolving area owing to current and potential applications of these materials in various electronic devices. This text aims to cover conduction in disordered solids from fundamental physical principles and theories, through practical material development with an emphasis on applications in all areas of electronic materials. International group of contributors Presents basic physical concepts developed in this field in recent years in a uniform manner Brings up-to-date, in a one-stop source, a key evolving area in
